

512K (64K x 8) Low-Voltage CMOS EPROM

FEATURES

- Wide voltage range 3.0V to 5.5V
- · High speed performance
 - 200 ns access time available at 3.0V
- · CMOS Technology for low power consumption
 - 12 mA Active current at 3.0V
 - 35 mA Active current at 5.5V
 - 100 µA Standby current
- · Factory programming available
- · Auto-insertion-compatible plastic packages
- Auto ID™ aids automated programming
- · Separate chip enable and output enable controls
- · High speed "Express" programming algorithm
- Organized 64K x 8: JEDEC standard pinouts
- 28-pin Dual-in-line package
- 32-pin PLCC package
- 28-pin SOIC package
- 28-pin TSOP package
- 28-pin VSOP package
- Tape and reel
- · Available for the following temperature ranges
 - Commercial:

0°C to +70°C

- Industrial:

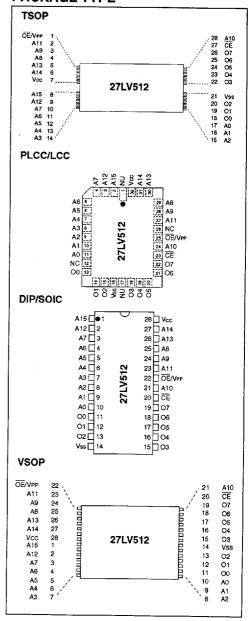
-40°C to +85°C

DESCRIPTION

The Microchip Technology Inc. 27LV512 is a low-voltage (3.0 volt) CMOS EPROM designed for battery powered applications. The device is organized as a 64K x 8 (64K-Byte) non-volatile memory product. The 27LV512 consumes only 12 mA maximum of active current during a 3.0 volt read operation therefore improving battery performance. This device is designed for very low-voltage applications where conventional 5.0 volt only EPROMs can not be used. Accessing individual bytes from an address transition or from power-up (chip enable pin going low) is accomplished in less than 200 ns at 3.0 volts. This device allows systems designers the ability to use low voltage non-volatile memory with today's low-voltage microprocessors and peripherals in battery powered applications.

A complete family of packages is offered to provide the most flexibility in applications. For surface mount applications, PLCC, SOIC or TSOP packaging is available. Tape and reel packaging is also available for PLCC or SOIC packages.

PACKAGE TYPE



1.0 ELECTRICAL CHARACTERISTICS

1.1 Maximum Ratings*

Vcc and input voltages w.r.t. Vss-0.6V to +7.25V

VPP voltage w.r.t. Vss during
programming-0.6V to +14.0V

Voltage on A9 w.r.t. Vss-0.6V to +13.5V

Output voltage w.r.t. Vss-0.6V to Vcc +1.0V

Storage temperature ...-65°C to +150°C

Ambient temp. with power applied ...-65°C to +125°C

TABLE 1-1: PIN FUNCTION TABLE

Name	Function
A0-A15	Address Inputs
CE	Chip Enable
ŌĒ/VPP	Output Enable/Programming Voltage
00 - 07	Data Output
Vcc	+3.0V To +5.5V Power Supply
Vss	Ground
NC	No Connection; No Internal Connection
NU	Not Used; No External Connection is Allowed

TABLE 1-2: READ OPERATION DC CHARACTERISTICS

				mercial:		.5V unless otherwise specified Tamb = 0°C to +70°C Tamb = -40°C to +85°C				
Parameter	Part*	Status	Symbol	Min.	Max.	Units	Conditions			
Input Voltages	all	Logic "1" Logic "0"	VIH VIL	2.0 -0.5	Vcc+1 0.8	>>	·			
Input Leakage	all		lu	-10	10	μА	VIN = 0 to VCC			
Output Voltages	all	Logic "1" Logic "0"	Voh Vol	2.4	0.45	>>	IOH = - 400 μA IOL = 2.1 mA			
Output Leakage	all	. —	ILO	-10	10	μА	Vout = 0V to Vcc			
Input Capacitance	all	-	CIN		6	pF	Vin = 0V; Tamb = 25°C; f = 1 MHz			
Output Capacitance	all	_	Соит	_	12	pF	Vout = 0V; Tamb = 25°C; f = 1 MHz			
Power Supply Current, Active	CI	TTL input	lccı lcc2	. <u>-</u>	35@5.0V 12@3.0V 45@5.0V 12@3.0V	mA mA mA mA	Vcc = 5.5V f = 1 MHz; OE/VPP = CE = VIL; IOUT = 0 mA; VIL = -0.1 to 0.8V; VIH = 2.0 to Vcc; Note 1			
Power Supply Current, Standby	C I all	TTL input TTL input CMOS input	ICC(S)TLL ICC(S)TLL ICC(S)CMOS	<u>-</u>	1@3.0V 2@3.0V 100@3.0V	mA mA μA	CE = Vcc ± 0.2V			

^{*} Parts: C=Commercial Temperature Range; I=Industrial Temperature Range

Note 1: Typical active current increases .75 mA per MHz up to operating frequency for all temperature ranges.

^{*}Notice: Stresses above those listed under "Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operation listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

TABLE 1-3: READ OPERATION AC CHARACTERISTICS

AC Testing Waveform: VIH = 2.4V and VIL = 0.45V; VOH = 2.0V and VOL = 0.8V 0 output Load: 1 TTL Load + 100 pF

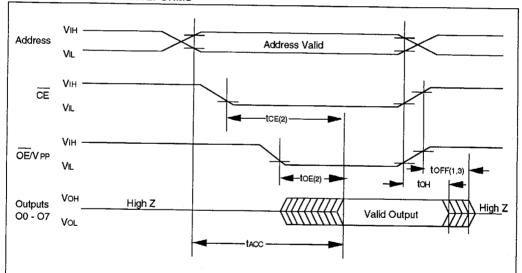
Input Rise and Fall Times: 10 ns

Ambient Temperature: Comm

Commercial: Tamb = 0°C to +70°C Industrial: Tamb = -40°C to +85°C

		ou a.		Iai	141110 = -40 C to +85 C						
Parameter	Sym	27LV512-20		27LV512-25		27LV512-30			_		
	Oy	Min	Max	Min	Max	Min	Max	Units	Conditions		
Address to Output Delay	tacc		200	_	250	_	300	ns	CE = OE = VIL		
CE to Output Delay	tce	_	200		250		300	ns	ŌĒ = VIL		
OE to Output Delay	toe	_	90	_	100		125	ns	CE = VIL		
CE or OE to O/P High Impedance	tOFF	0	50	0	50	0	50	ns			
Output Hold from Address CE or OE, whichever goes first	toн	0	_	0	_	0		ns			

FIGURE 1-1: READ WAVEFORMS



Notes: (1) toff is specified for OE/VPP or CE, whichever occurs first

(2) OE may be delayed up to tcE - toE after the falling edge of CE without impact on tcE

(3) This parameter is sampled and is not 100% tested.

TABLE 1-4: PROGRAMMING DC CHARACTERISTICS

	Ambient Temperature: Tamb = 25° C $\pm 5^{\circ}$ C VCC = 6.5 V ± 0.25 V, \overrightarrow{OE} /VPP = VH = 13.0 V ± 0.25 V							
Parameter	Status	Symbol	Min.	Max.	Units	Conditions (See Note 1)		
Input Voltages	Logic "1" Logic "0"	Vih Vil	2.0 -0.1	Vcc+1 0.8	V V			
Input Leakage	_	IJ	-10	10	μΑ	VIN = 0V to VCC		
Output Voltages	Logic "1" Logic "0"	Voh Vol	2.4	0.45	V V	10H = -400 μA IOL = 2.1 mA		
Vcc Current, program & verify	_	ICC2	_	35	mA			
OE/VPP Current, program	_	IPP2	_	25	mA	CE = VIL		
A9 Product Identification	_	ViD	11.5	12.5	٧			

Note 1: Vcc must be applied simultaneously or before VPP voltage on OE/VPP and removed simultaneously or after the VPP voltage on OE/VPP.

TABLE 1-5: PROGRAMMING AC CHARACTERISTICS

for Program, Program Verify and Program Inhibit Modes	Ambient Tempera	AC Testing Waveform: ViH=2.4V and ViL=0.45V; VOH=2.0V; VOL=0.8V Ambient Temperature: Tamb=25°C \pm 5°C VCC = 6.5V \pm 0.25V, \overrightarrow{OE} /VPP = VH = 13.0V \pm 0.25 V								
Parameter	,	Symbol	Min.	Max.	Units	Remarks				
Address Set-Up Time		tas	2		μs					
Data Set-Up Time		tos	2_		μs					
Data Hold Time		tDH	2		μs					
Address Hold Time		tan	0		μs					
Float Delay (2)		tor	0	130	ns					
Vcc Set-Up Time		tvcs	2		μs					
Program Pulse Width (1)		tPW	95	105	μs	100 μs typical				
CE Set-Up Time		tces	2		μs					
OE Set-Up Time		toes	2		μs					
OE Hold Time		toeh	2		μs					
OE Recovery Time		ton	2	_	μs					
OE/VPP Rise Time During Program	nming	tPRT	50	-	ns					

Note 1: For express algorithm, initial programming width tolerance is 100 μs $\pm 5\%.$

Note 2: This parameter is only sampled and not 100% tested. Output float is defined as the point where data is no longer driven (see timing diagram).

FIGURE 1-2: PROGRAMMING WAVEFORMS

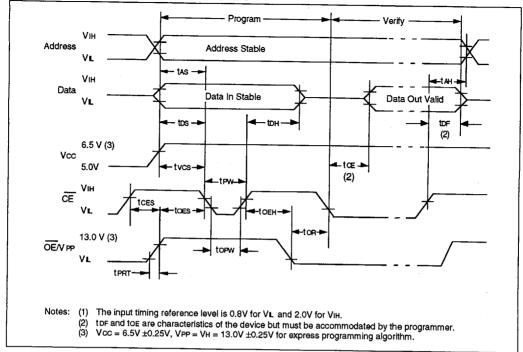


TABLE 1-6: MODES

Operation Mode	CE	OE/VPP A9		O0 - O7
Read	ad Vil		X	Dout
Program	VIL	VH	x	Din
Program Verify	VIL	VIL	x	Dout
Program inhibit	ViH	VH	x	High Z
Standby	ViH	x	x	High Z
Output Disable	VIL	ViH	x	High Z
Identity	VIL	VIL	VH	Identity Code

X = Don't Care

1.2 Read Mode

(See Timing Diagrams and AC Characteristics)

Read Mode is accessed when

- a) the CE pin is low to power up (enable) the chip
- b) the OE/VPP pin is low to gate the data to the output pins.

For Read operations, if the addresses are stable, the address access time (tacc) is equal to the delay from $\overline{\text{CE}}$ to output (tcE). Data is transferred to the output after a delay (toE) from the falling edge of $\overline{\text{OE}}/\text{VPP}$.

1.3 Standby Mode

The standby mode is defined when the CE pin is high and a program mode is not identified.

1.4 Output Enable OE/VPP

This multifunction pin eliminates bus connection in microprocessor based systems in which multiple devices may drive the bus. The outputs go into a high impedance state when:

• the OE/VPP pin is high (VIH).

When a VH input is applied to this pin, it supplies the programming voltage (VPP) to the device.

1.5 Programming Mode

The Express algorithm has been developed to improve on the programming throughput times in a production environment. Up to ten 100-microsecond pulses are applied until the byte is verified. A flowchart of the Express algorithm is shown in Figure 1-3.

Programming takes place when:

- a) Vcc is brought to the proper voltage,
- b) OE/VPP is brought to the proper VH level, and
- c) CE line is low.

Since the erased state is "1" in the array, programming of "0" is required. The address to be programmed is set via pins A0 - A15 and the data to be programmed is presented to pins O0 - O7. When data and address are stable, a low going pulse on the $\overline{\text{CE}}$ line programs that location.

1.6 Verify

After the array has been programmed it must be verified to ensure all the bits have been correctly programmed. This mode is entered when all the following conditions are met:

- a) Vcc is at the proper level,
- b) the OE/VPP pin is low, and
- c) the CE line is low.

1.7 Inhibit

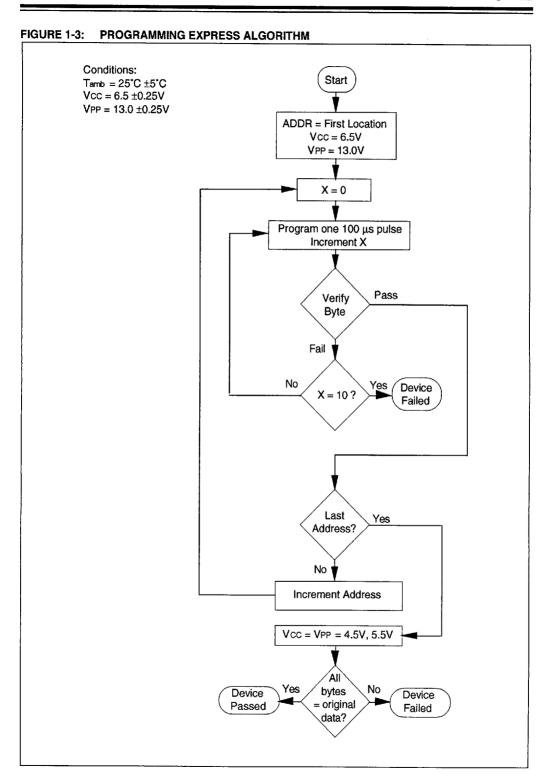
When programming multiple devices in parallel with different data, only CE needs to be under separate control to each device. By pulsing the CE line low on a particular device, that device will be programmed; all other devices with CE held high will not be programmed with the data (although address and data will be available on their input pins).

1.8 Identity Mode

In this mode specific data is output which identifies the manufacturer as Microchip Technology Inc. and the device type. This mode is entered when Pin A9 is taken to VH (11.5V to 12.5V). The $\overline{\text{CE}}$ and $\overline{\text{OE}}/\text{VPP}$ lines must be at VIL. A0 is used to access any of the two non-erasable bytes whose data appears on O0 through O7.

Pin →	Input	Output								
ldentity ↓	AO	0 7	0	O 5	0	O 3	0	0	0	Н ө х
Manufacturer Device Type*	VIL VIH	0	0	1 0	0	1	0	0 0	1	29 0D

^{*} Code subject to change



27LV512 Product Identification System

To order or to obtain information, e.g., on pricing or delivery, please use the listed part numbers, and refer to the factory or the listed sales offices.

